

Title (en)
NISI SPUTTERING TARGET WITH IMPROVED GRAIN STRUCTURE

Title (de)
NISI-SPUTTERTARGET MIT VERBESSERTER KORNSTRUKTUR

Title (fr)
CIBLE DE PULVÉRISATION NISI À STRUCTURE DE GRAIN AMÉLIORÉE

Publication
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Application
EP 19182532 A 20190626

Priority
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Abstract (en)
The present invention relates to a sputtering target comprising a NiSi alloy comprising from 2 to 8 weight% Si, and to a process for forming said sputtering target.

IPC 8 full level
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CPC (source: EP)
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Citation (applicant)
• US 2008138974 A1 20080612 - LI YANPING [US], et al
• US 6780295 B2 20040824 - IVANOV EUGENE Y [US]

Citation (search report)
• [A] US 2006118407 A1 20060608 - IVANOV EUGENE Y [US]
• [AD] US 6780295 B2 20040824 - IVANOV EUGENE Y [US]
• [T] SPIEKERMANN P: "Legierungen - ein besonderes patentrechtliches Problem?", MITTEILUNGEN DER DEUTSCHEN PATENTANWAELTE, HEYMANN, KOLN, DE, vol. 34, 1 January 1993 (1993-01-01), pages 178 - 190, XP002152326, ISSN: 0026-6884

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BA ME

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EP 3757248 A1 20201230; **EP 3757248 B1 20220413**; MY 195195 A 20230111; WO 2020260094 A1 20201230

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EP 19182532 A 20190626; EP 2020066782 W 20200617; MY PI2021007065 A 20200617